

AMENDMENTS TO THE CLAIMS:

1. (Currently Amended) A capillary used to ~~perform wire bonding~~ first bond a wire to an external electrode and then bond the wire to a top-surface electrode of a semiconductor device, the capillary having a face surface formed at a tip end thereof, the face surface inclining toward a center thereof so as to have a tapered shape, the capillary having a through hole formed therethrough so as to permit wire to be placed therethrough, the through hole having an opening at the center of the face surface,

wherein an angle of inclination of the face surface relative to a plane perpendicular to an axis of the capillary and including the opening of the through hole is in a range from 4° to 15°, and a height of the face surface along the axis of the capillary is equal to or greater than a thickness of the wire, and

wherein, when seen in a side sectional view including the axis of the capillary, a width of the face surface in a direction perpendicular to the axis of the capillary is greater than a width of the semiconductor device.

2. (Original) A capillary as claimed in claim 1, wherein the angle of inclination of the face surface is in a range from 8° to 12°.

3. (Canceled)

4. (Original) A method of wire bonding including steps of bonding wire to an external electrode and then bonding the wire to a top-surface electrode of a semiconductor device,

wherein a capillary as claimed in claim 1 is used to perform wire bonding.

5. (Original) A method of wire bonding as claimed in claim 4, wherein a load applied to the capillary when the wire is pressed and deformed with the face surface of the capillary so as to bond to the top-surface electrode of the semiconductor device is in a range from 100 to 200 g/cm².

6. (New) A method of wire bonding comprising:

bonding a first end of the wire to an external electrode using a capillary, the capillary having a face surface formed at a tip end, and inclining toward a center thereof, so as to have a tapered shape, the capillary also having a through hole to permit a wire to be placed therethrough, the through hole having an opening at the center of the face surface, and an angle of inclination of the face surface relative to a plane perpendicular to an axis of the capillary and including the opening of the through hole is in a range from 4° to 15°; and

bonding a second end of the wire to a top-surface electrode of a semiconductor device using the capillary,

wherein the capillary, when seen in a side sectional view including the axis of the capillary, has a width of the face surface in a direction perpendicular to the axis of the capillary that is greater than a width of the semiconductor device.

7. (New) The method of claim 6, wherein the capillary has a height of the face surface along the axis of the capillary that is equal to or greater than a thickness of the wire.

8. (New) The method of claim 6, wherein the capillary has a uniform angle of inclination.